

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
29 September 2005 (29.09.2005)

PCT

(10) International Publication Number
WO 2005/091394 A1

(51) International Patent Classification⁷: H01L 51/00

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(21) International Application Number:
PCT/JP2005/005306

(22) International Filing Date: 16 March 2005 (16.03.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2004-087077 24 March 2004 (24.03.2004) JP

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG,
KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG,
MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH,
PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

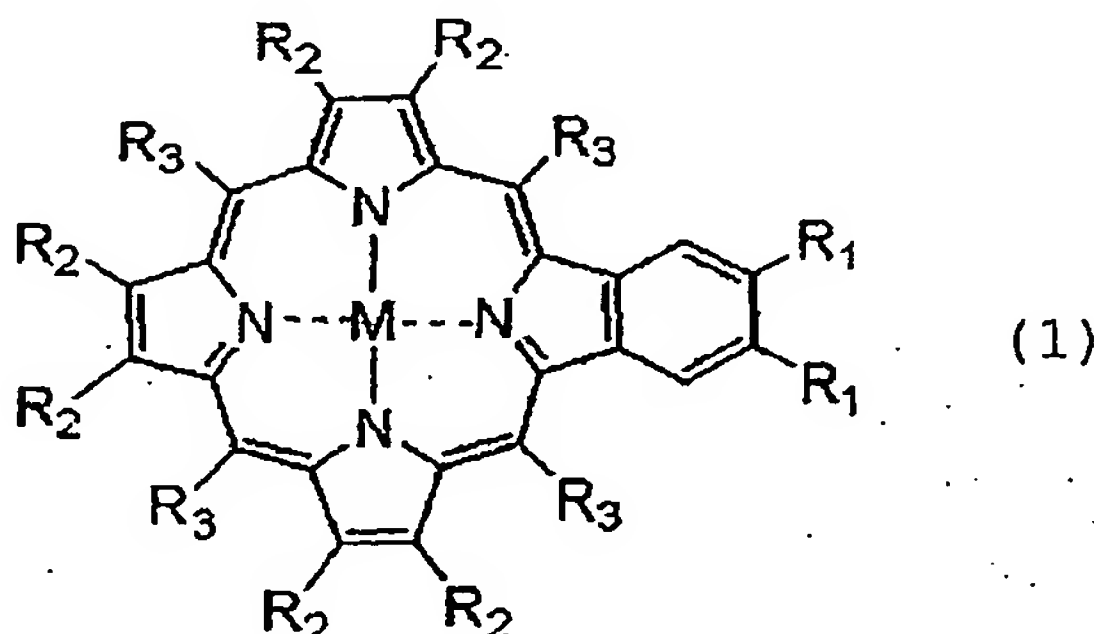
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO,
SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN,
GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: FIELD EFFECT TRANSISTOR AND METHOD OF PRODUCING SAME



(57) Abstract: A field effect transistor is provided which
comprises an organic semiconductor layer comprising
a compound having a monobenzoporphyrin skeleton
represented by the general formula (1): wherein R₁ and
R₂ are independently selected from the group consisting
of a hydrogen atom, a halogen atom, a hydroxyl group,
and alkyl, alkenyl, oxyalkyl, thioalkyl, alkyl ester and aryl
groups each having 1 to 12 carbon atoms with the proviso
that adjacent R₁ may be the same or different and adjacent
R₂ may be the same or different and that at least two of R₂
are not hydrogen atoms; R₃ is a hydrogen atom or an aryl
group; and M denotes two hydrogen atoms, a metal atom
or a metal oxide.

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